

## IV1D12020T3 – 1200V 20A SiC Schottky Diode

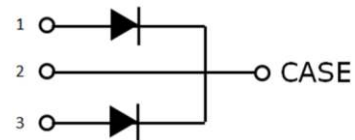
### Features:

- Max Junction Temperature 175°C
- High Surge Current Capacity
- Zero Reverse Recovery Current
- Zero Forward Recovery Voltage
- High-Frequency Operation
- Temperature independent switching behavior
- Positive Temperature Coefficient on  $V_F$

### Applications:

- Solar Power Boost
- Inverter Free Wheeling Diodes
- Vienna 3-Phase PFC
- AC/DC Converters
- Switch Mode Power Supplies

### Package



Part Number	Package
IV1D12020T3	TO247-3

### Absolute Maximum Ratings (Tc=25°C unless otherwise specified)

Symbol	Parameter	Value	Unit
$V_{RRM}$	Reverse voltage (repetitive peak)	1200	V
$V_{DC}$	DC blocking voltage	1200	V
$I_F$	Forward current (continuous) @Tc=25°C	30*	A
	Forward current (continuous) @Tc=135°C	15.2*	A
	Forward current (continuous) @Tc=155°C	10*	A
$I_{FSM}$	Surge non-repetitive forward current sine halfwave @Tc=25°C tp=10ms	72*	A
$P_{tot}$	Total power dissipation @ Tc=25°C	176*	W
	Total power dissipation @ Tc=150°C	29*	
$\int i^2 dt$	$I^2t$ value @Tc=25°C tp=10ms	26*	A <sup>2</sup> S
Tstg	Storage temperature range	-55 to 175	°C
Tj	Operating junction temperature range	-55 to 175	°C

\* Per Leg

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

## Electrical Characteristics

Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note
$V_F$	Forward Voltage	1.56 2.2	1.8 3	V	$I_F = 20\text{ A } T_J = 25^\circ\text{C}$ $I_F = 20\text{ A } T_J = 175^\circ\text{C}$	Fig. 1
$I_R$	Reverse Current	5 25	100 350	$\mu\text{A}$	$V_R = 1200\text{ V } T_J = 25^\circ\text{C}$ $V_R = 1200\text{ V } T_J = 175^\circ\text{C}$	Fig. 2
C	Total Capacitance	1150		pF	$V_R = 1\text{ V}, T_J = 25^\circ\text{C}, f = 1\text{ MHz}$	Fig. 3
		118			$V_R = 400\text{ V}, T_J = 25^\circ\text{C}, f = 1\text{ MHz}$	
		85			$V_R = 800\text{ V}, T_J = 25^\circ\text{C}, f = 1\text{ MHz}$	
$Q_C$	Total Capacitive Charge	124		nC	$V_R = 800\text{ V}, T_J = 25^\circ\text{C},$ $Q_C = \int_0^{V_R} C(V)dV$	Fig. 4

## Thermal Characteristics

Symbol	Parameter	Typ.	Unit	Note
$R_{th(j-c)}$	Thermal Resistance from Junction to Case	0.85*	$^\circ\text{C/W}$	Fig.7

\* Per Leg

## Typical Performance

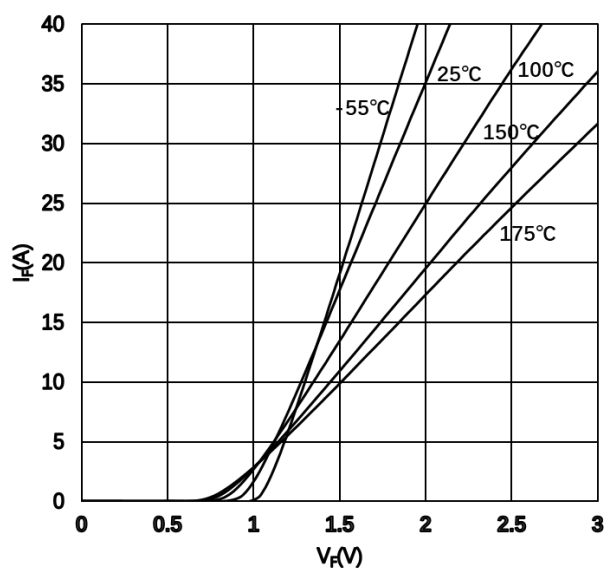


Figure 1. Typical Forward Characteristics

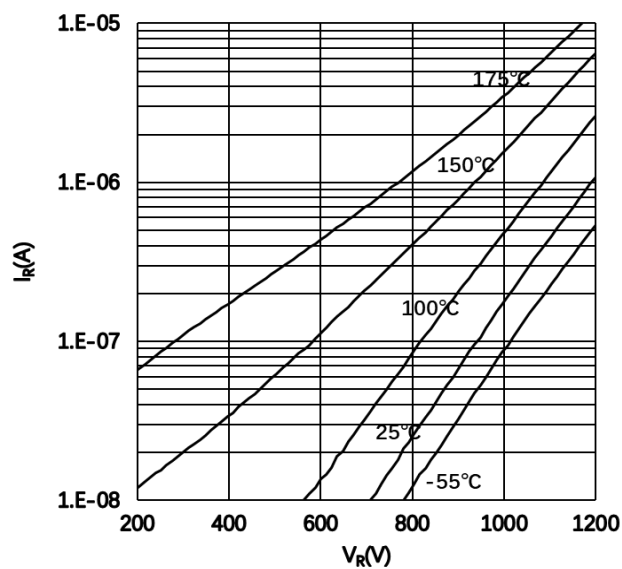


Figure 2. Typical Reverse Characteristics

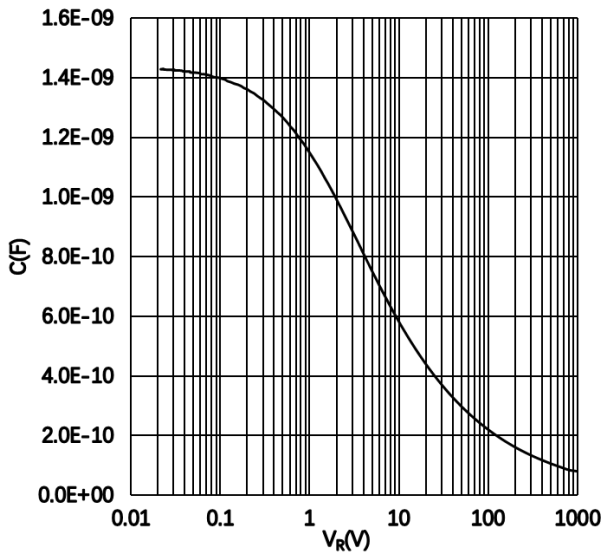


Figure 3. Capacitance vs. Reverse Voltage

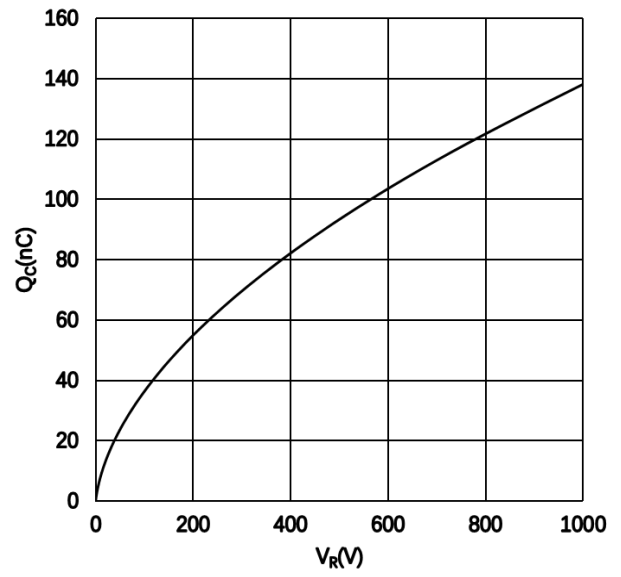


Figure 4. Recovery Charge vs. Reverse Voltage

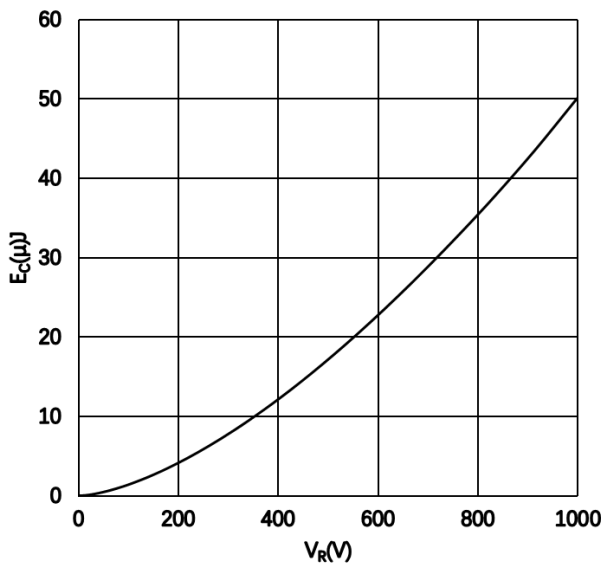


Figure 5. Capacitance Stored Energy

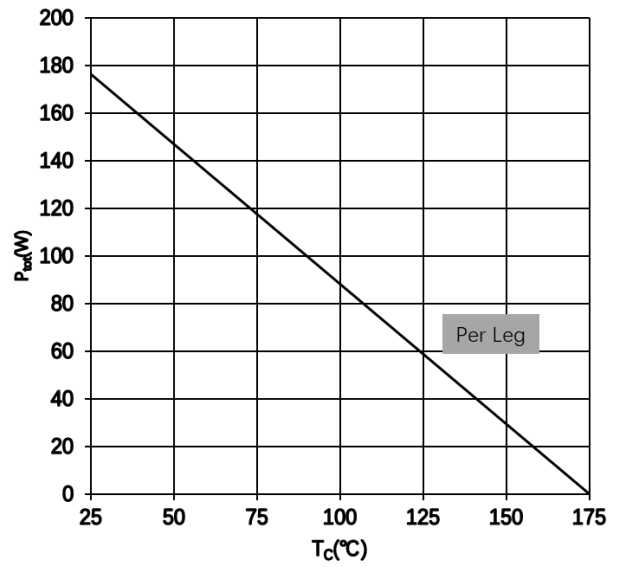


Figure 6. Power Derating

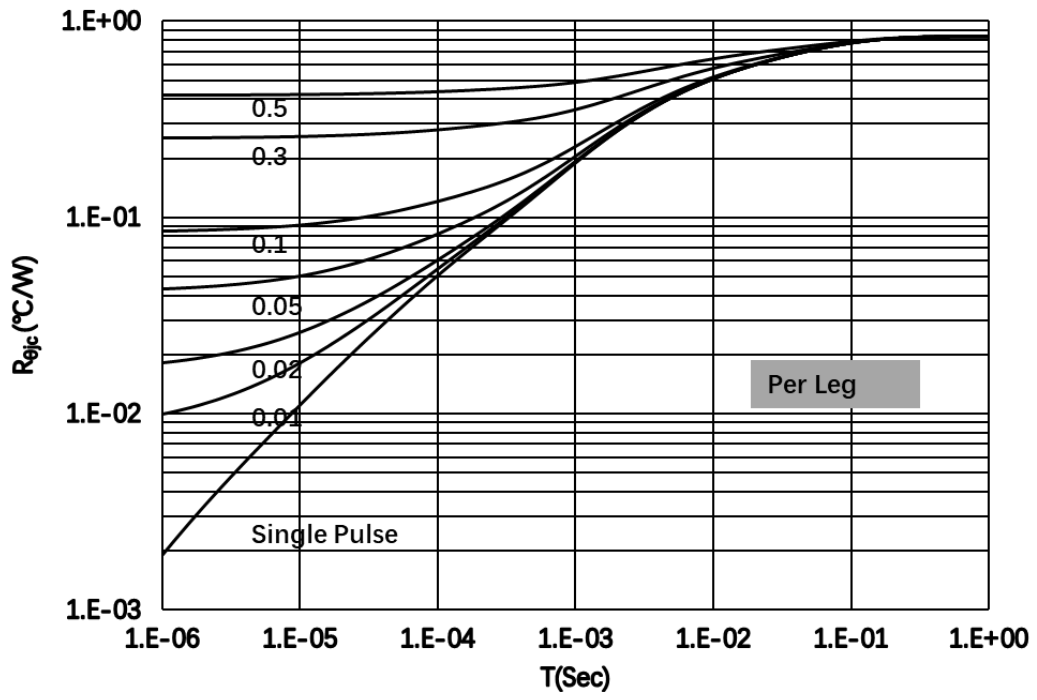
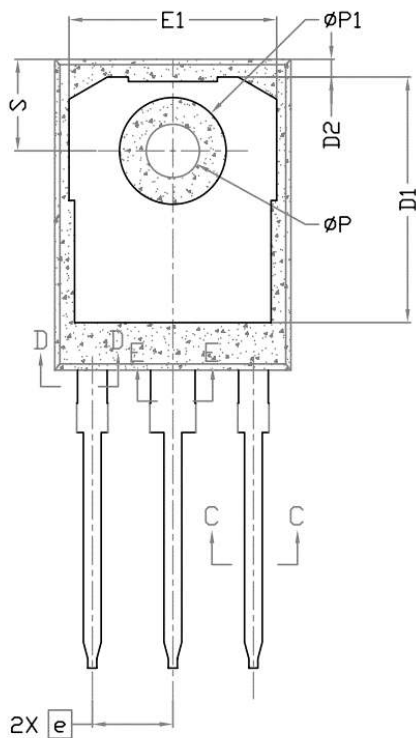
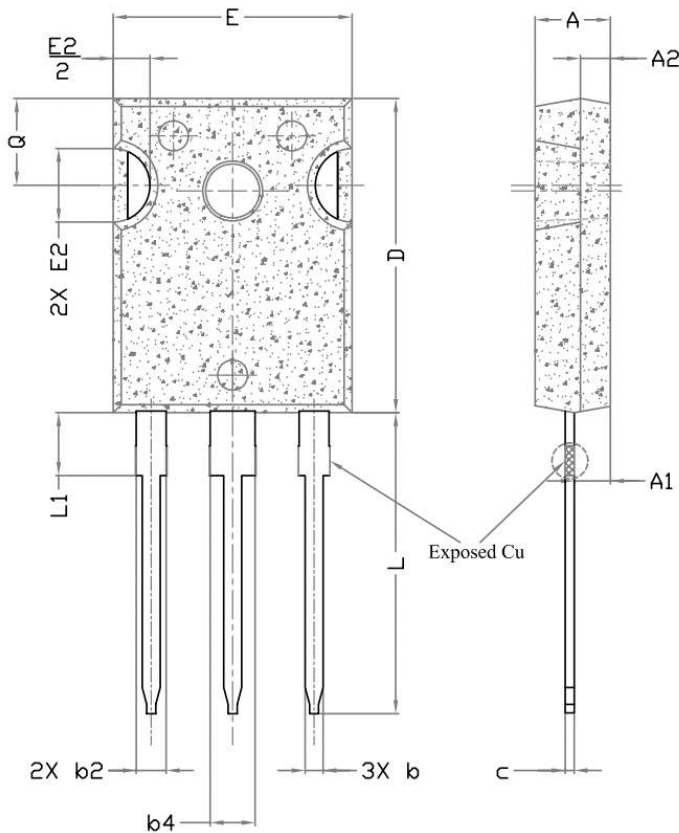
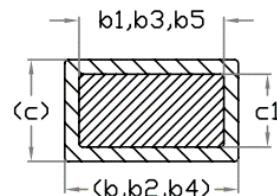


Figure 7. Transient Thermal Impedance

## Package Dimensions



SYMBOL	DIMENSIONS			NOTES
	MIN.	NOM.	MAX.	
A	4.83	5.02	5.21	
A1	2.29	2.41	2.55	
A2	1.50	2.00	2.49	
b	1.12	1.20	1.33	
b1	1.12	1.20	1.28	
b2	1.91	2.00	2.39	6
b3	1.91	2.00	2.34	
b4	2.87	3.00	3.22	6, 8
b5	2.87	3.00	3.18	
c	0.55	0.60	0.69	6
c1	0.55	0.60	0.65	
D	20.80	20.95	21.10	4
D1	16.25	16.55	17.65	5
D2	0.51	1.19	1.35	
E	15.75	15.94	16.13	4
E1	13.46	14.02	14.16	5
E2	4.32	4.91	5.49	3
e	5.44BSC			
L	19.81	20.07	20.32	
L1	4.10	4.19	4.40	6
ØP	3.56	3.61	3.65	7
ØP1	7.19REF.			
Q	5.39	5.79	6.20	
S	6.04	6.17	6.30	



Section C--C,D--D,E--E

### Note:

1. Package Reference: JEDEC TO247, Variation AD
2. All Dimensions Are In mm
3. Slot Required, Notch May Be Rounded
4. Dimension D&E Do Not Include Mold Flash

## Notes

For further information please contact IVCT' Office.

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